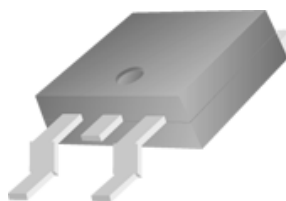


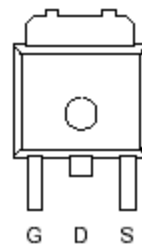
N-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize High Cell Density process. Low $r_{DS(on)}$ assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are PWMDC-DC converters, power management in portable and battery-powered products such as computers, printers, battery charger, telecommunication power system, and telephones power system.

- Low $r_{DS(on)}$ Provides Higher Efficiency and Extends Battery Life
- Miniature TO-252 Surface Mount Package Saves Board Space
- High power and current handling capability
- Low side high current DC-DC Converter applications



TO-252



Top View

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ m(Ω)	I_D (A)
30	59 @ $V_{GS} = 10V$	24
	88 @ $V_{GS} = 4.5V$	20

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ^a	$T_C = 25^\circ C$	I_D	24	A
Pulsed Drain Current ^b		I_{DM}	40	
Continuous Source Current (Diode Conduction) ^a		I_S	30	A
Power Dissipation ^a	$T_C = 25^\circ C$	P_D	50	W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 175	$^\circ C$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	50	$^\circ C/W$
Maximum Junction-to-Case	$R_{\theta JC}$	3.0	$^\circ C/W$

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

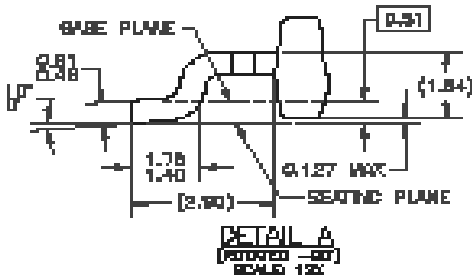
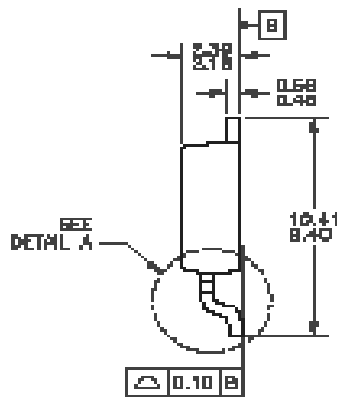
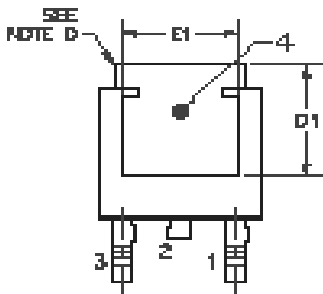
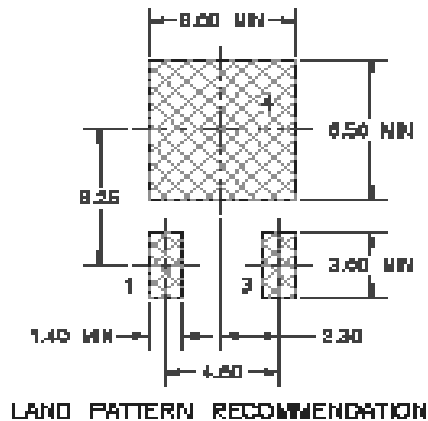
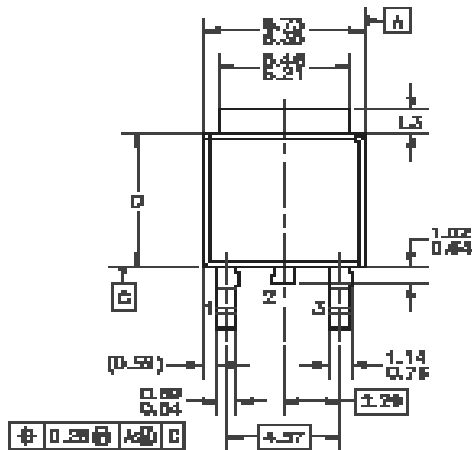
SPECIFICATIONS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	1.0			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA
		$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^\circ\text{C}$			25	
On-State Drain Current ^A	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	34			A
Drain-Source On-Resistance ^A	$r_{DS(on)}$	$V_{GS} = 10 \text{ V}, I_D = 12 \text{ A}$			59	m Ω
		$V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$			88	
Forward Transconductance ^A	g_{fs}	$V_{DS} = 15 \text{ V}, I_D = 12 \text{ A}$		22		S
Diode Forward Voltage	V_{SD}	$I_S = 24 \text{ A}, V_{GS} = 0 \text{ V}$		1.1		V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$ $I_D = 10 \text{ A}$		4.0		nC
Gate-Source Charge	Q_{gs}			1.1		
Gate-Drain Charge	Q_{gd}			1.4		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 25 \text{ V}, R_L = 25 \Omega, I_D = 24 \text{ A},$ $V_{GEN} = 10 \text{ V}$		16		nS
Rise Time	t_r			5		
Turn-Off Delay Time	$t_{d(off)}$			23		
Fall-Time	t_f			3		
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 24 \text{ A}, di/dt = 100 \text{ A}/\mu\text{S}$		50		

Notes

- Pulse test: $PW \leq 300\mu\text{s}$ duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

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Package Information



- NOTES: UNLESS OTHERWISE SPECIFIED
- A) ALL DIMENSIONS ARE IN MILLIMETERS.
 - B) THIS PACKAGE CONFORMS TO JEDEC, TO-262, ISSUE C, VARIATION AA, 31 DE, DATED NOV. 1989.
 - C) DIMENSIONING AND TOLERANCING PER ASME Y14.00M-1994.
 - D) HEAT SINK TOP EDGE COULD BE IN CHAMFERED CORNERS OR EDGE PROTRUSION.
 - E) DIMENSIONS L3, D, E1 AND D1 TABLE:

	SECTION AA	SECTION AB
L3	0.68-1.27	1.62-2.54
D	0.97-0.99	0.93-0.99
E1	4.32 MIN	3.91 MIN
D1	3.81 MIN	4.37 MIN